NSN 5961-00-163-6955

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View Online at https://aerobasegroup.com/nsn/5961-00-163-6955

Inclosure Material:
Metal
Overall Length:
1.253 inches
End Application:
Missile, mx peacekeeper
Mounting Facility Quantity:
1
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
0.438 inches
Thread Size:
0.190 inches
Criticality Code Justification:
Feat
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
13.00 regulator voltage
Voltage Tolerance In Percent:
-5.0 to 5.0
Current Rating Per Characteristic:
190.00 milliamperes all primaries horsepower metric and 750.00 milliamperes dc current in reverse breakdown region
Power Rating Per Characteristic:
10.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius ambient air
Special Features:
Design analysis
Nuclear Hardness Critical Feature:
Hardened
Test Data Document:
98747-89108805 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Thread Series Designator:
Unf

Terminal Type And Quantity:

1 threaded stud and 1 tab, solder lug

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N/a

Unit Of Measure:

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Demilitarization:

No

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